

GaN FET Test Kit 2.0



➤ Features:

- GaN Test Kit based on AccoTEST Standard test platform STS8200
- Up to quad site test by one kit, max support 2 test kit with 8 sites test in parallel by the tester
- Fully Floating VI source driven up to 1000V/10A DC
- Low leakage test module included, <1nA Leakage test ability
- Support menu-driven programming
- Support Dynamic Ron Soft Switching Test
- Support soft docking

➤ Specification (DC):

- Drain to Source

Test Items	Force/Measure Voltage Ranges	Resolution	Accuracy (%FS)	Remark
BVDSS/IDSS	±1000V, ±500V, ±200V, ±100V	16bit	±0.05%	HVI1K
Test_VD_Sweeps_GDS Test_High_ISB Test_VD_GDS_Sub_Id	±1000V, ±500V, ±200V, ±100V	16bit	±0.05%	By HVI1K/FOVI
Test_Vg_Id Test_Vg_Id_Ig Test_Vg_Id_Ron	±100V, ±40V, ±20V, ±10V, ±5V, ±2V, ±1V	16bit	±0.05%	By FPVI/FOVI



BVDSS/IDSS /VFSD/RDSON Test_Vg_Id_Ron	$\pm 100V, \pm 40V, \pm 20V,$ $\pm 10V, \pm 5V, \pm 2V, \pm 1V$	16bit	$\pm 0.05\%$	FPVI10_PLUS
Test Items	Force Current Ranges	Resolution	Accuracy (%FS)	Remark
VFSD/RDSON Test_Vg_Id_Ron	$\pm 10A$ (Pulsed)	16bit	$\pm 0.5\%$	FPVI10_PLUS
Test Items	Low Leakage Measure Current Ranges	Resolution	Accuracy	Remark
IDSS	$\pm 10mA$	16bit	$\pm 0.1\%FS$	By HVI1K
Test_VD_Sweeps_GDS Test_High_ISB Test_VD_GDS_Sub_Id	$\pm 1mA$	16bit	$\pm (3\mu A + 0.2\%)$	by HV-PAM
	$\pm 100\mu A$	16bit	$\pm (300nA + 0.2\%)$	by HV-PAM
	$\pm 10\mu A$	16bit	$\pm (50nA + 0.5\%)$	by HV-PAM
	$\pm 1\mu A$	16bit	$\pm (10nA + 0.5\%)$	by HV-PAM
Test Items	Low VDson Measure Ranges	Resolution	Accuracy (%FS)	Remark
RDSON/VDSON Test_Vg_Id_Ron	$\pm 100mV$	16bit	$\pm 1\%$	by QVM
	$\pm 10mV$	16bit	$\pm 1\%$	by QVM
	$\pm 1mV$	16bit	$\pm 2\%$	by QVM

- Gate to Source

Test Items	Force/Measure Voltage Ranges	Resolution	Accuracy(%FS)	Remark
VTH/IGSSF/ IGSSR/BVGS	$\pm 40V, \pm 20V, \pm 10V,$ $\pm 5V, \pm 2V, \pm 1V$	16bit	$\pm 0.05\%$	By FOVI/FPVI
Test Items	Force /Measure Current Ranges	Resolution	Accuracy(%FS)	Remark
VTH/IGSSF/ IGSSR/BVGSS	$\pm 100mA, \pm 10mA,$ $\pm 1mA, \pm 100\mu A$	16bit	$\pm 0.1\%$	By FOVI
	$\pm 1A$ (Pulsed) , $\pm 10\mu A$ (measure only)	16bit	$\pm 0.5\%$	By FOVI
Test Items	Low Leakage Measure Current Ranges	Resolution	Accuracy(%FS)	Remark
IGSSF/IGSSR/ Test_Vg_Ig_Step	$\pm 1mA$	16bit	$\pm (1.5\mu A + 0.15\%)$	by LV-PAM
	$\pm 100\mu A$	16bit	$\pm (150nA + 0.15\%)$	by LV-PAM
	$\pm 10\mu A$	16bit	$\pm (15nA + 0.15\%)$	by LV-PAM
	$\pm 1\mu A$	16bit	$\pm (1.5nA + 0.15\%)$	by LV-PAM
	$\pm 100nA$	16bit	$\pm (0.3nA + 0.1\%)$	by LV-PAM



➤ **Specification (Dynamic Ron Soft Switching) :**

- HV Stress Voltage : $\leq +1000V$.
- HV Stress Time : 0~>10S.
- Gate Driver: -30V ~+30V (Windows 30V)
- Toff: <2us
- Tdelay: <10us.
- Id: <10A

